



2SJ665

P-Channel Power MOSFET -100V, -27A, 77mΩ, TO-263-2L

ON Semiconductor®

<http://onsemi.com>

Features

- ON-resistance $R_{DS(on)1}=59m\Omega$ (typ.)
- Input capacitance $C_{iss}=4200pF$ (typ.)
- 4V drive

Specifications

Absolute Maximum Ratings at $T_a=25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		-100	V
Gate-to-Source Voltage	V_{GS}		± 20	V
Drain Current (DC)	I_D		-27	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	-108	A
Allowable Power Dissipation	P_D	$T_c=25^\circ C$	65	W
Channel Temperature	T_{ch}		150	$^\circ C$
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$
Avalanche Energy (Single Pulse) *1	E_{AS}		48	mJ
Avalanche Current *2	I_{AV}		-27	A

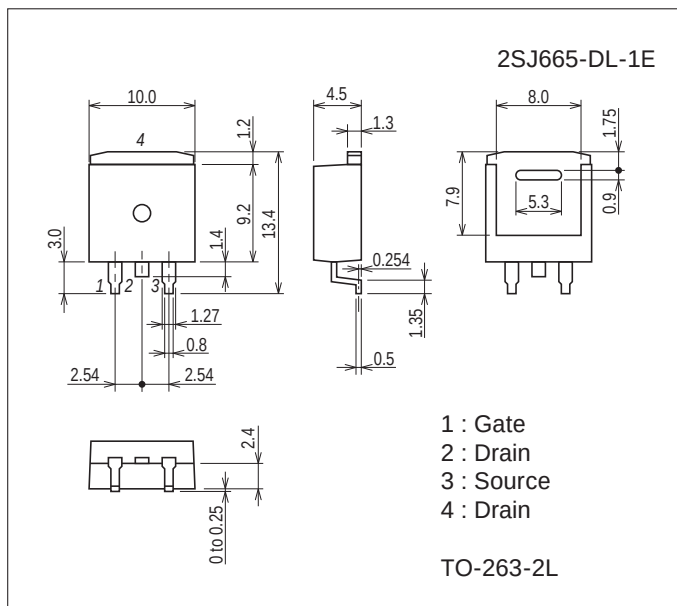
Note : *1 $V_{DD}=-30V$, $L=100\mu H$, $I_{AV}=-27A$ (Fig.1)*2 $L \leq 100\mu H$, single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

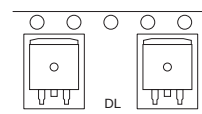
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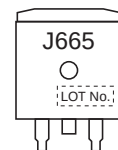
Product & Package Information

- Package : TO-263-2L
- JEITA, JEDEC : SC-83, TO-263
- Minimum Packing Quantity : 800 pcs./reel

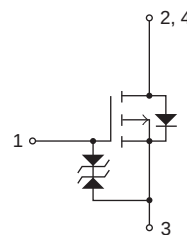
Packing Type: DL



Marking



Electrical Connection



2SJ665

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-1mA, V_{GS}=0V$	-100			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-100V, V_{GS}=0V$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=-10V, I_D=-1mA$	-1.2		-2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-10V, I_D=-14A$	15	25		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=-14A, V_{GS}=-10V$		59	77	$m\Omega$
	$R_{DS(on)2}$	$I_D=-14A, V_{GS}=-4V$		75	105	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=-20V, f=1MHz$		4200		pF
Output Capacitance	C_{oss}			280		pF
Reverse Transfer Capacitance	C_{rss}			220		pF
Turn-ON Delay Time	$t_{d(on)}$	See Fig.2		30		ns
Rise Time	t_r			150		ns
Turn-OFF Delay Time	$t_{d(off)}$			330		ns
Fall Time	t_f			135		ns
Total Gate Charge	Q_g	$V_{DS}=-50V, V_{GS}=-10V, I_D=-27A$		74		nC
Gate-to-Source Charge	Q_{gs}			12.8		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			14.7		nC
Diode Forward Voltage	V_{SD}	$I_S=-27A, V_{GS}=0V$		-0.98	-1.2	V

Fig.1 Avalanche Resistance Test Circuit

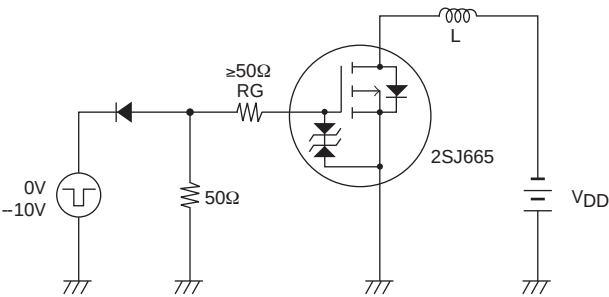
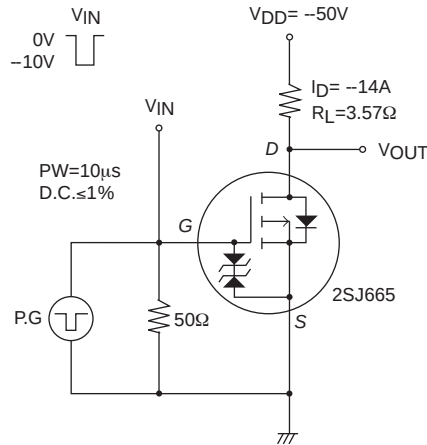
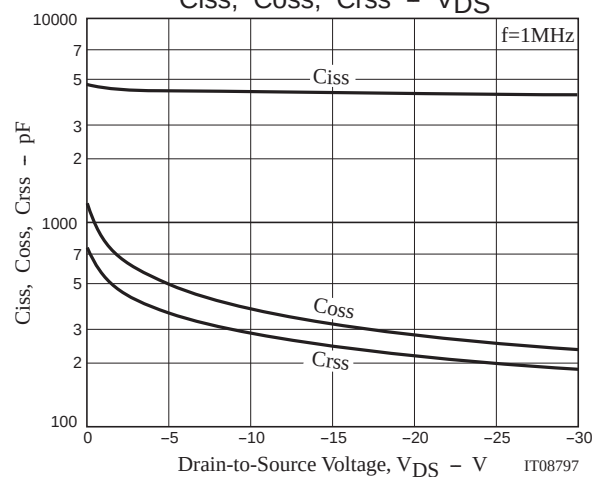
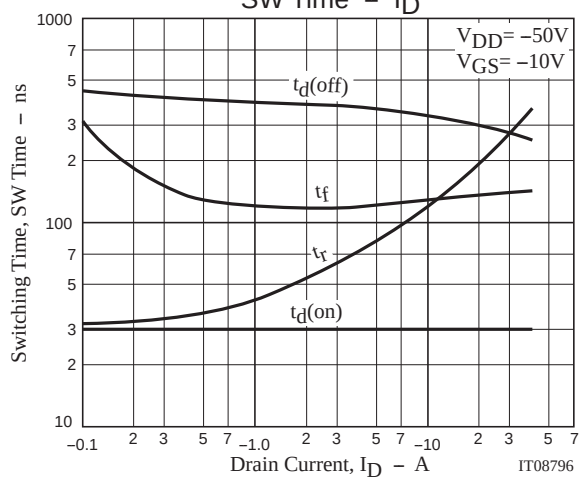
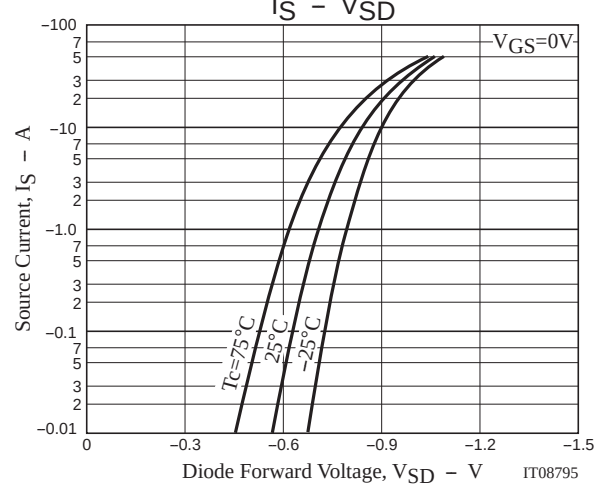
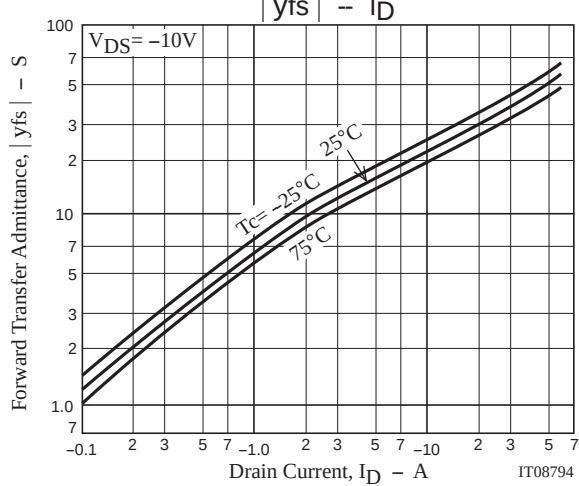
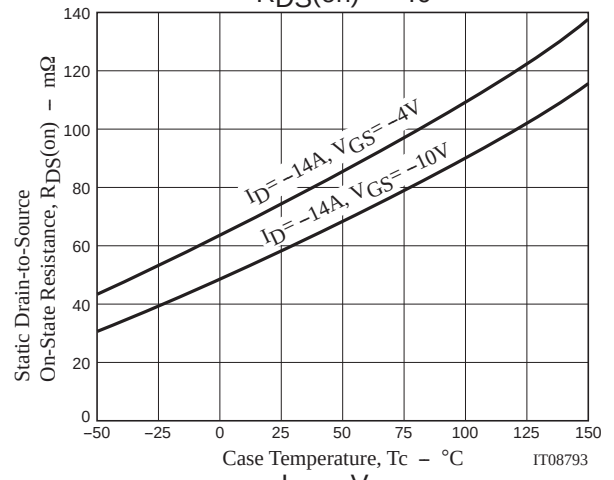
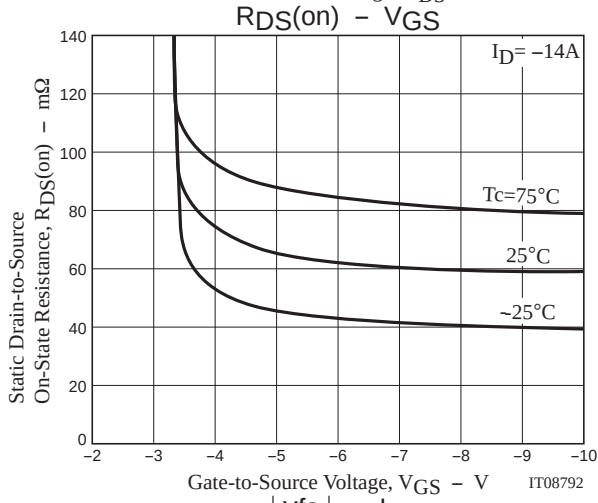
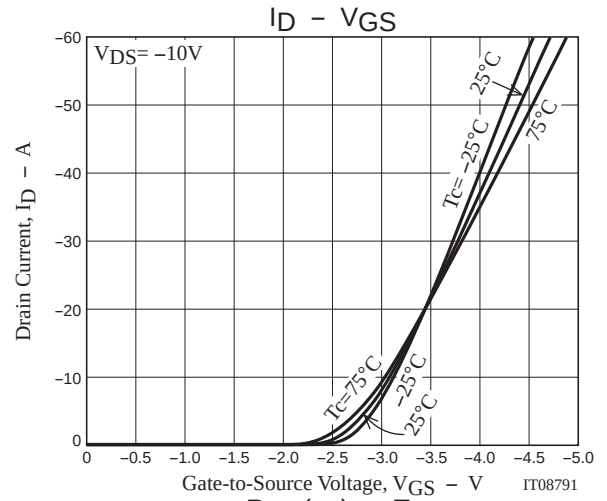
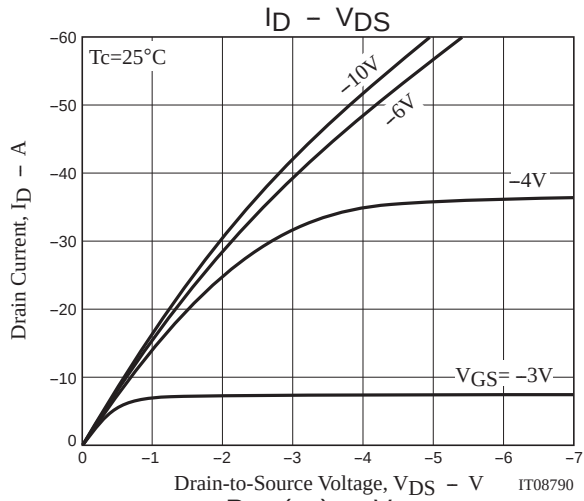


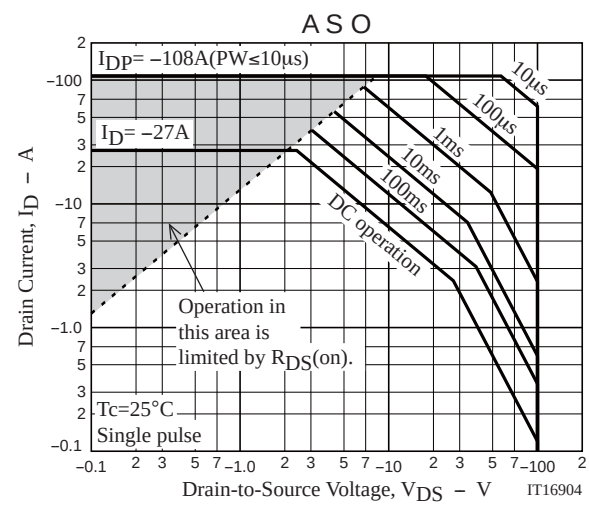
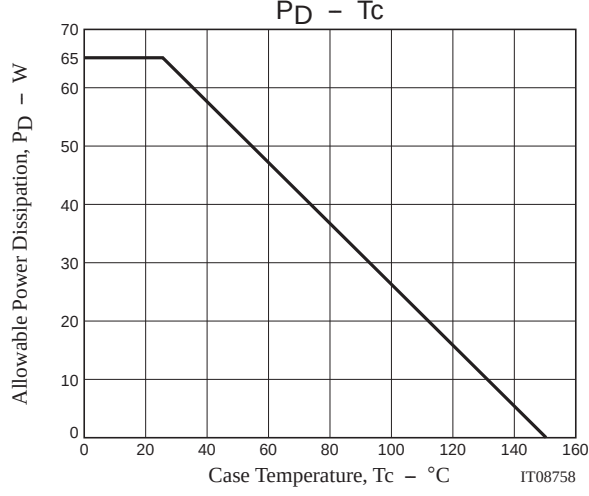
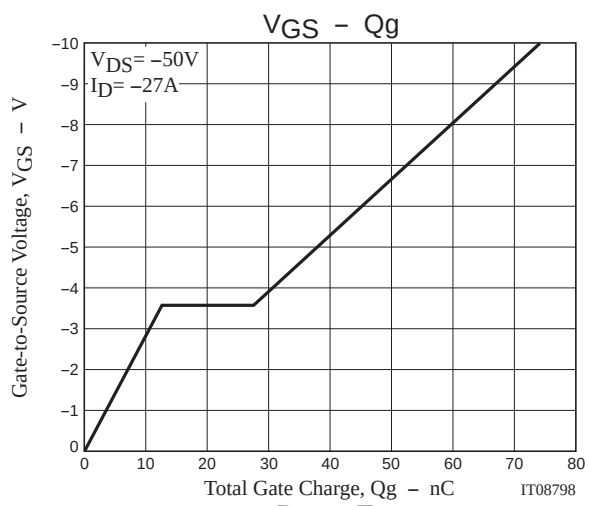
Fig.2 Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
2SJ665-DL-1E	TO-263-2L	800pcs./reel	Pb Free





Taping Specification

2SJ665-DL-1E

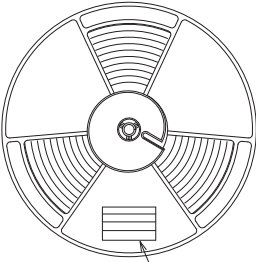
1. Packing Format

Package Name	Maximum Number of devices contained (pcs)			Packing format	
	Reel	Inner box	Outer box	Inner BOX	Outer BOX
TO-263-2L	800	1600	6400	SPD-0V0011 2 reel contained Dimensions:mm (external) 351×340×68	SPD-0V0009 4 inner boxes contained Dimensions:mm (external) 390×370×318

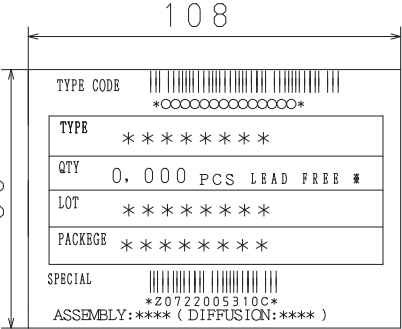
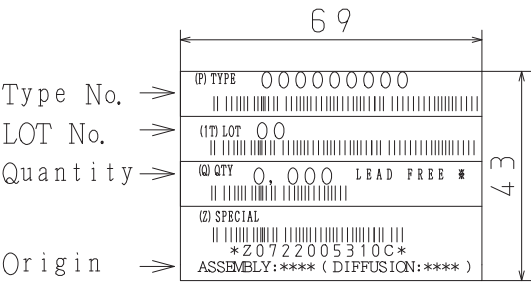
Reel label, Inner box label
(unit:mm)

Outer box label

Packing method



Reel label

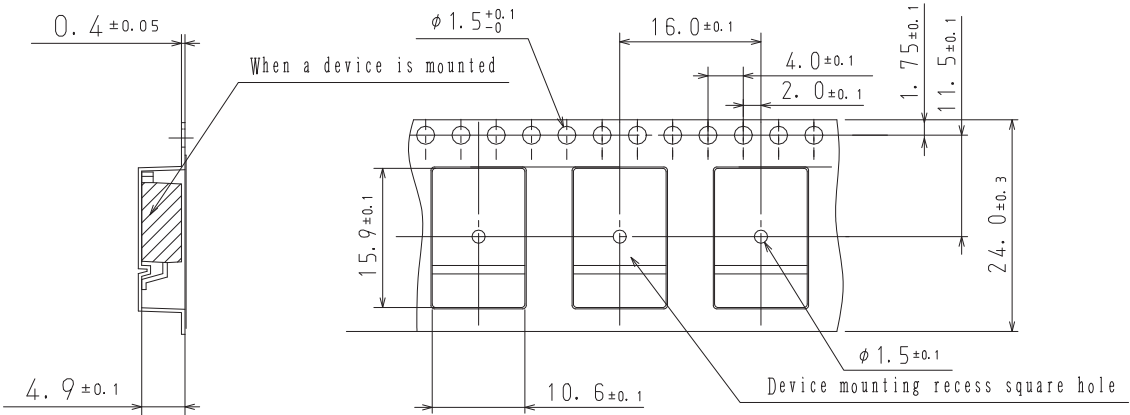


NOTE (1)
The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

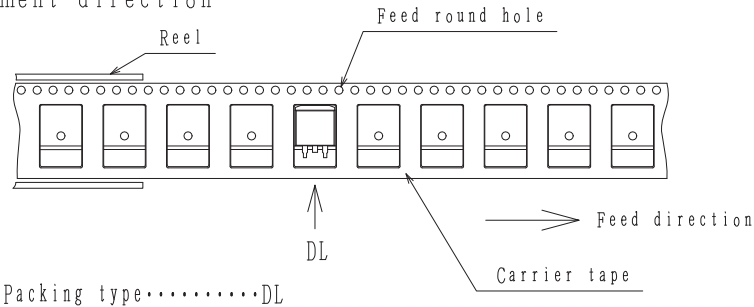
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A

2. Taping configuration

2-1. Carrier tape size (unit:mm)

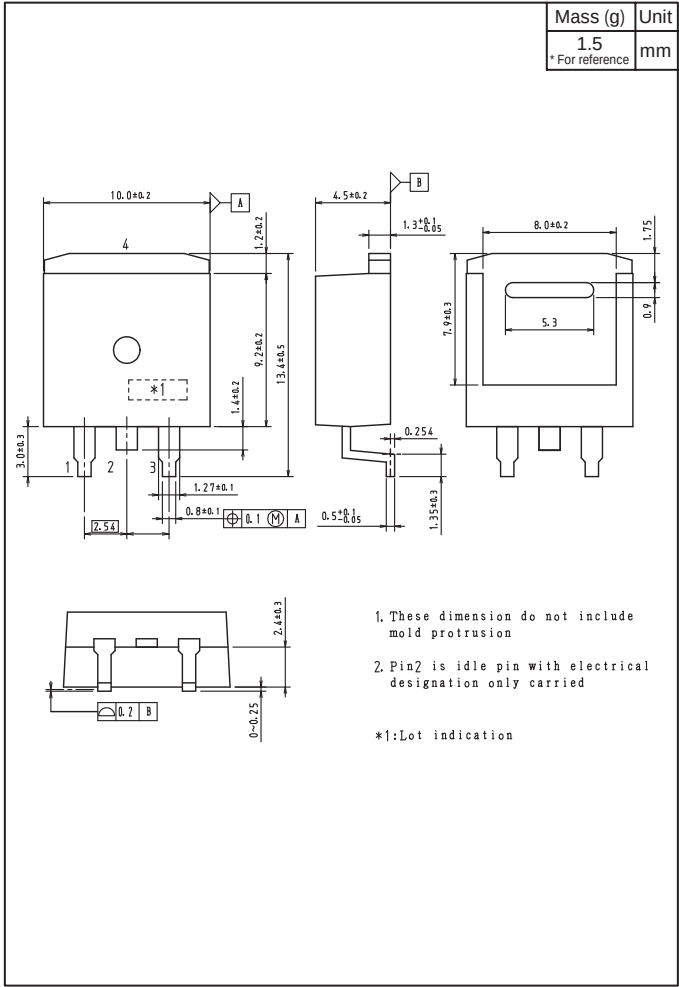


2-2. Device placement direction

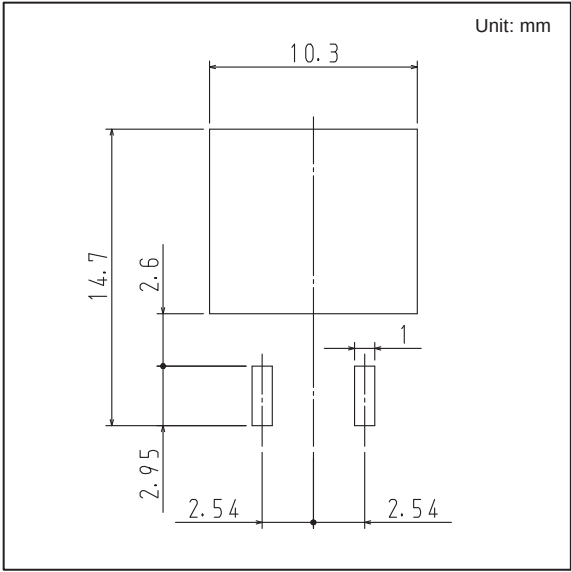


Outline Drawing

2SJ665-DL-1E



Land Pattern Example



Note on usage : Since the 2SJ665 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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